MMBT2222A



MMBT2222A SOT-23 Plastic-Encapsulate Transistors(NPN)

General description

SOT-23 Plastic-Encapsulate Transistors(NPN)

FEATURES

- Complementary to MMBT2907A
- Power Dissipation of 300mW
- High Stability and High Reliability
- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0



DEVICE MARKING CODE:

Device Type	Device Marking
MMBT2222A	1P

. Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	Vсво	75	V
Collector-Emitter Voltage	VCEO	40	V
Emitter -Base Voltage	Vebo	6	V
Collector Current-Continuous	lc	600	mA
Collector Power Dissipation	Pc	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55-+150	°C
Thermal resistance From junction to ambient	Reja	417	°C/W

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Cumphiala	Test Condition	Limits		Unit
Parameter	Symbols	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=10uA, IE=0	75		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=10mA, IB=0	40		V
Emitter-base breakdown voltage	V(BR)EBO	IE=10uA, IC=0	6		V
Collector cut-off current	ICEX	VCE=30V, VEB(off)=3V		10	nA
Collector cut-off current	Ісво	VCB=60V, IE=0		10	nA
Emitter cut-off current	IEBO	VEB=3V, IC=0		100	nA
DC current gain	hFE(1)*	VCE=10V, IC=150mA	100	300	
	hFE(2)*	VCE=10V, IC=0.1mA	40		
	hFE(3)*	VCE=10V, IC=500mA	42		
Collector-emitter saturation voltage	VCE(sat)1*	IC=500mA, IB=50mA		1.00	V
Collector-emitter saturation voltage	VCE(sat)2*	IC=150mA, IB=15mA		0.30	V
Base -emitter saturation voltage	VBE(sat)1*	IC=500mA, IB=50mA		2.00	V
Base -emitter saturation voltage	VBE(sat)2*	IC=150mA, IB=15mA		1.20	V
Transition frequency	fT	VCE=20V, IC=20mA,f=100MHz	300		MHz
Delay time	td	VCC=30V, VBE(off)=-0.5V, IC=150mA,		10	nS
Rise time	tr	IB1=15mA		25	nS
Storage time	ts			225	nS
Fall time	tf	VCC=30V, IC=150mA, IB1=IB2=15mA		60	nS

*Pulse test: pulse width \leq 300us, duty cycle \leq 2.0%

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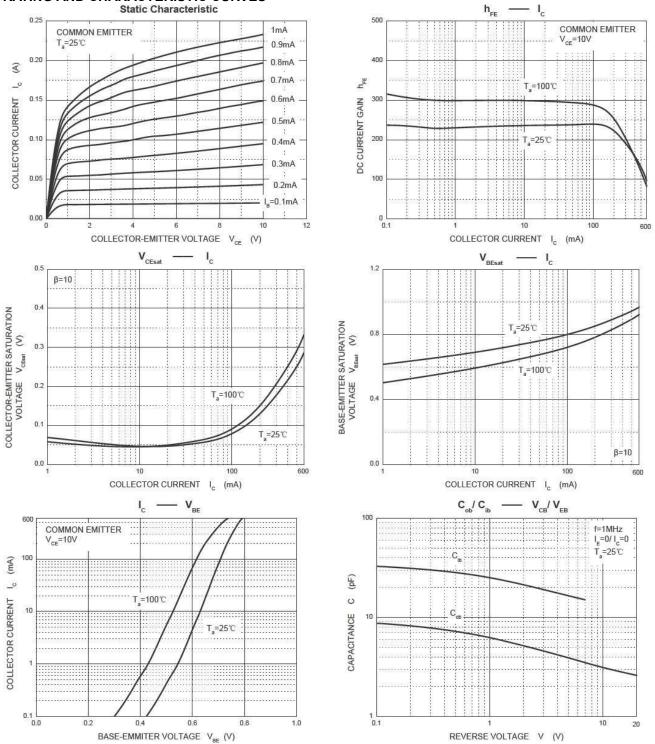
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CLASSIFICATION OF hFE(1)

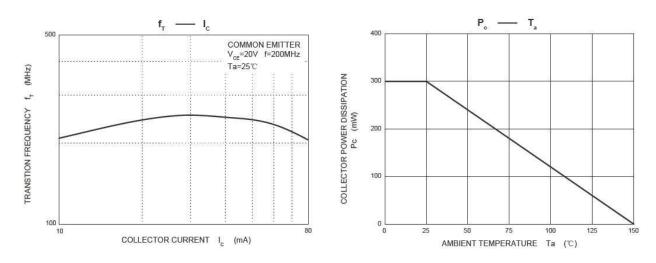
HFE	100-300		
RANK	L	Н	
RANGE	100-200	200-300	

RATING AND CHARACTERISTIC CURVES

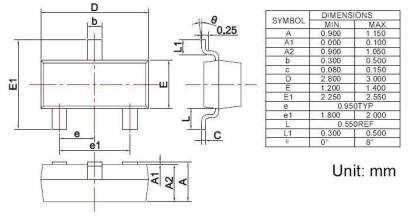


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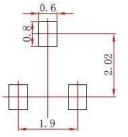


SOT-23 PACKAGE OUTLINE Plastic surface mounted package



Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note: 1.Controlling dimension:In millimeters, 2.General tolerance:± 0.05mm, 3.The pad layout is for reference purposes only,



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